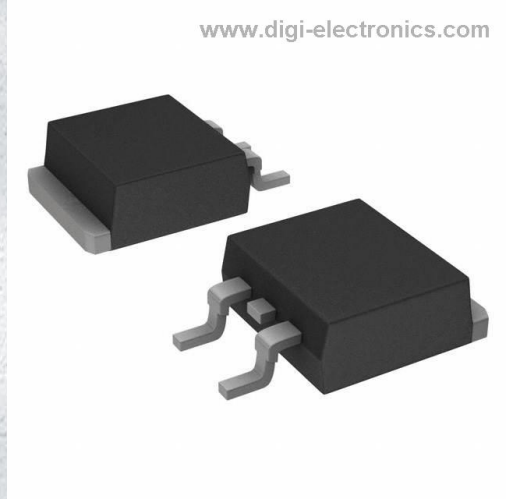
NTD80N02G Datasheet



DiGi Electronics Part Number	NTD80N02G-DG
Manufacturer	onsemi
Manufacturer Product Number	NTD80N02G
Description	MOSFET N-CH 24V 80A DPAK
Detailed Description	N-Channel 24 V 80A (Tc) 75W (Tc) Surface Mount D PAK

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NTD80N02G	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
24 V	80A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	5.8mOhm @ 80A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250µA	42 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	2600 pF @ 20 V
FET Feature:	Power Dissipation (Max):
-	75W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
DPAK	TO-252-3, DPAK (2 Leads + Tab), SC-63
Base Product Number:	
NTD80	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

ON Semiconductor

Is Now

To learn more about onsemi™, please visit our website at
www.onsemi.com

NTD80N02

Power MOSFET

24 V, 80 A, N−Channel DPAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Features

- These Devices are Pb−Free and are RoHS Compliant

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	24	Vdc
Gate−to−Source Voltage − Continuous	V_{GS}	±20	Vdc
Drain Current − Continuous @ T_C = 25°C − Single Pulse (t_p = 10 μs)	I_D I_{DM}	80* 200	Adc
Total Power Dissipation @ T_C = 25°C	P_D	75	Watts
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C
Single Pulse Drain−to−Source Avalanche Energy − Starting T_J = 25°C (V_{DD} = 24 Vdc, V_{GS} = 10 Vdc, I_L = 17 Apk, L = 5.0 mH, R_G = 25 Ω)	E_{AS}	733	mJ
Thermal Resistance − Junction−to−Case − Junction−to−Ambient (Note 1) − Junction−to−Ambient (Note 2)	 $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	 1.65 67 120	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from case for 10 seconds	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted to an FR4 board using 1″ pad size, (Cu Area 1.127 in^2).
2. When surface mounted to an FR4 board using the minimum recommended pad size, (Cu Area 0.412 in^2).

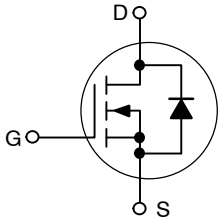
*Chip current capability limited by package.

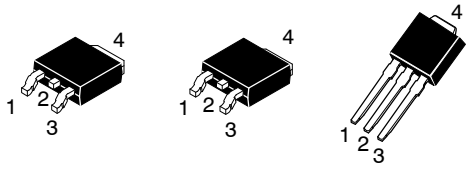
ON Semiconductor®

http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
24 V	5.0 mΩ	80 A

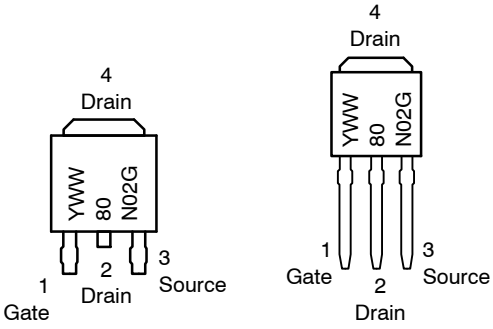
N−Channel





CASE 369AA DPAK (Surface Mount) STYLE 2 | **CASE 369C DPAK (Surface Mount) STYLE 2** | **CASE 369D DPAK (Straight Lead) STYLE 2**

MARKING DIAGRAMS & PIN ASSIGNMENTS



80N02	= Device Code
Y	= Year
WW	= Work Week
G	= Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTD80N02

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage (Note 3) (V_{GS} = 0 Vdc, I_D = 250 μAdc) Positive Temperature Coefficient		$V_{(BR)DSS}$	 24 –	 27 25	 – –	Vdc mV/°C
Zero Gate Voltage Drain Current (V_{GS} = 0 Vdc, V_{DS} = 24 Vdc) (V_{GS} = 0 Vdc, V_{DS} = 24 Vdc, T_J = 125°C)		I_{DSS}	 – –	 – –	 1.0 10	μAdc
Gate−Body Leakage Current (V_{GS} = ±20 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±100	nAdc
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage (Note 3) (V_{DS} = V_{GS}, I_D = 250 μAdc) Negative Threshold Temperature Coefficient		$V_{GS(th)}$	 1.0 –	 1.9 −3.8	 3.0 –	Vdc mV/°C
Static Drain−to−Source On−Resistance (Note 3) (V_{GS} = 10 Vdc, I_D = 80 Adc) (V_{GS} = 4.5 Vdc, I_D = 40 Adc) (V_{GS} = 10 Vdc, I_D = 20 Adc) (V_{GS} = 4.5 Vdc, I_D = 20 Adc)		$R_{DS(on)}$	 – – – 	 5.0 7.5 5.0 7.5	 5.8 9.0 5.8 9.0	mΩ
Forward Transconductance (V_{DS} = 15 Vdc, I_D = 10 Adc) (Note 3)		g_{FS}	–	20	–	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 20 Vdc, V_{GS} = 0 V, f = 1.0 MHz)	C_{iss}	–	2250	2600	pF
Output Capacitance		C_{oss}	–	900	1100	
Transfer Capacitance		C_{rss}	–	400	525	
SWITCHING CHARACTERISTICS (Note 4)						
Turn−On Delay Time	(V_{GS} = 4.5 Vdc, V_{DD} = 20 Vdc, I_D = 20 Adc, R_G = 2.5 Ω)	$t_{d(on)}$	–	17	30	ns
Rise Time		t_r	–	67	125	
Turn−Off Delay Time		$t_{d(off)}$	–	28	45	
Fall Time		t_f	–	40	75	
Gate Charge	(V_{GS} = 4.5 Vdc, I_D = 20 Adc, V_{DS} = 20 Vdc) (Note 3)	Q_T	–	30	42	nC
		Q1	–	7.0	12	
		Q2	–	18	28	
SOURCE−DRAIN DIODE CHARACTERISTICS						
Forward On−Voltage (I_S = 20 Adc, V_{GS} = 0 Vdc) (Note 3) (I_S = 40 Adc, V_{GS} = 0 Vdc) (I_S = 20 Adc, V_{GS} = 0 Vdc, T_J = 150°C)		V_{SD}	 – – –	 0.92 1.05 0.70	 1.2 – –	Vdc
Reverse Recovery Time	(I_S = 20 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs) (Note 3)	t_{rr}	–	38	52	ns
		t_a	–	20	–	
		t_b	–	18	–	
Reverse Recovery Stored Charge		Q_{rr}	–	0.038	–	μC

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

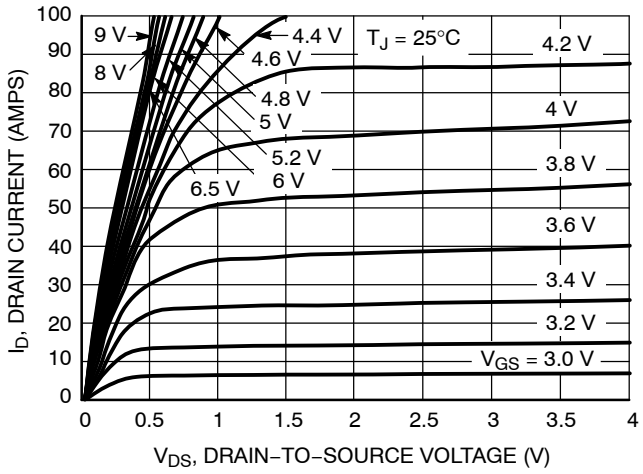


Figure 1. On−Region Characteristics

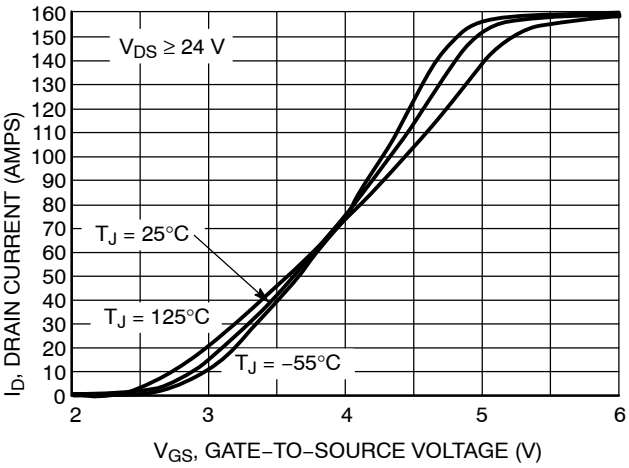


Figure 2. Transfer Characteristics

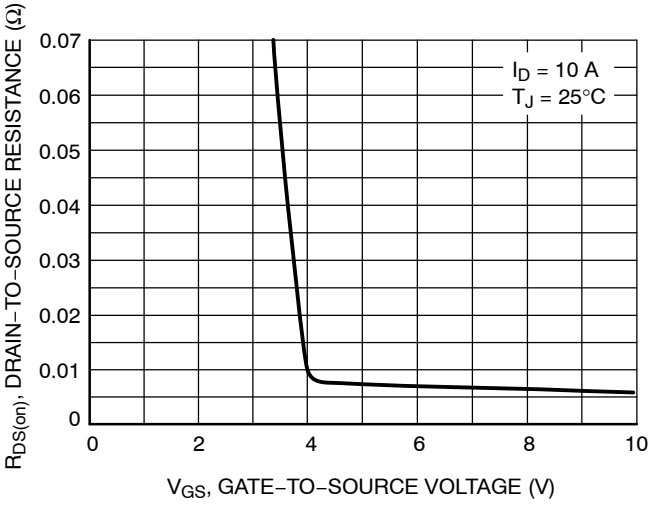


Figure 3. On−Resistance versus Gate−To−Source Voltage

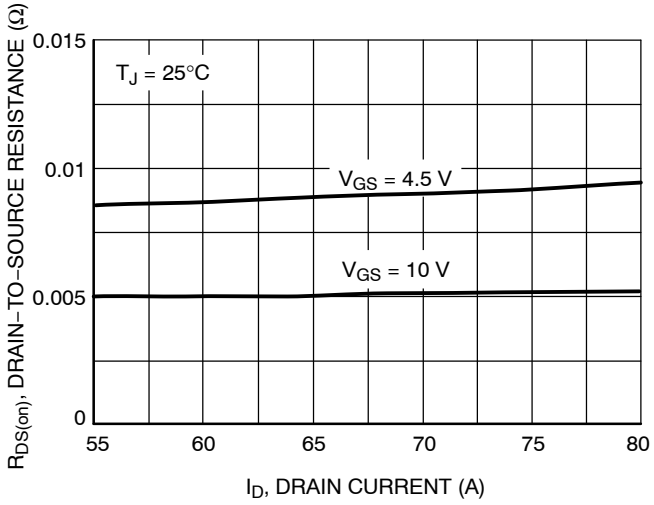


Figure 4. On−Resistance versus Drain Current and Gate Voltage

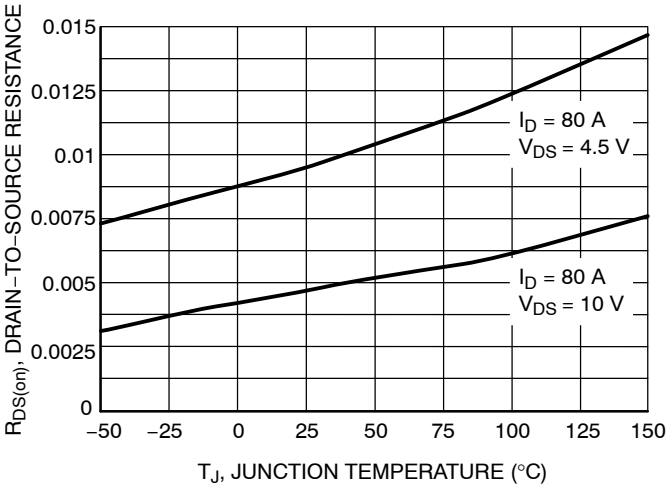


Figure 5. On−Resistance Variation with Temperature

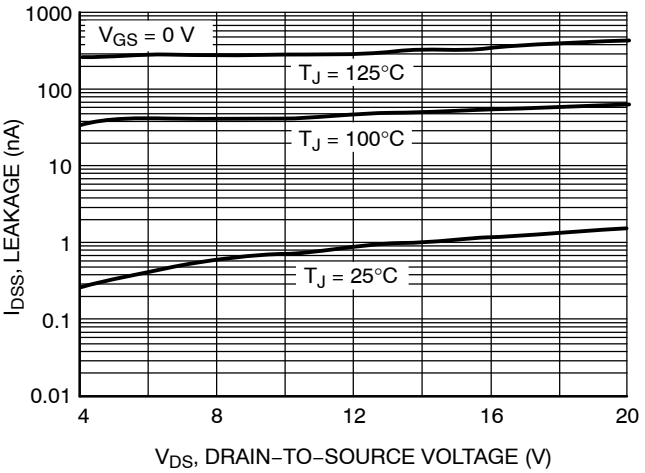


Figure 6. Drain−To−Source Leakage Current versus Voltage

TYPICAL CHARACTERISTICS

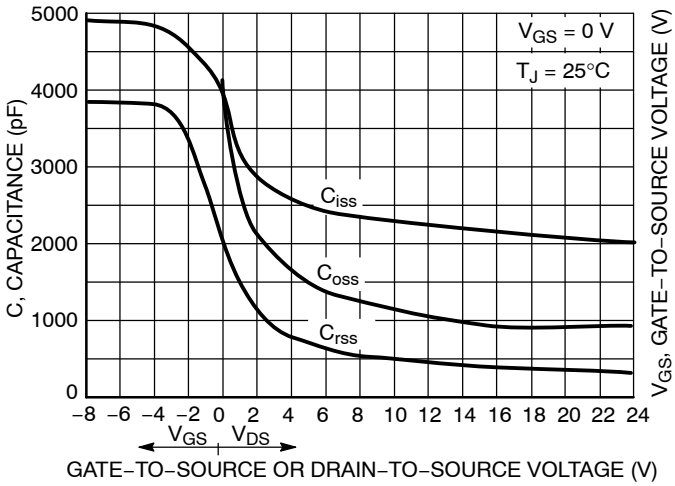


Figure 7. Capacitance Variation

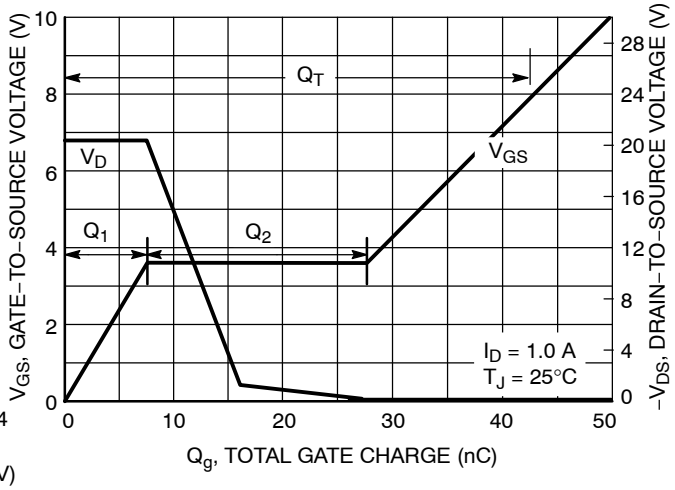


Figure 8. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

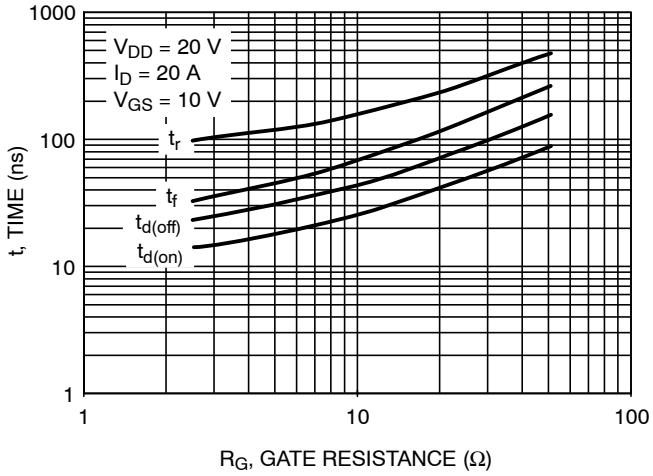


Figure 9. Resistive Switching Time Variation versus Gate Resistance

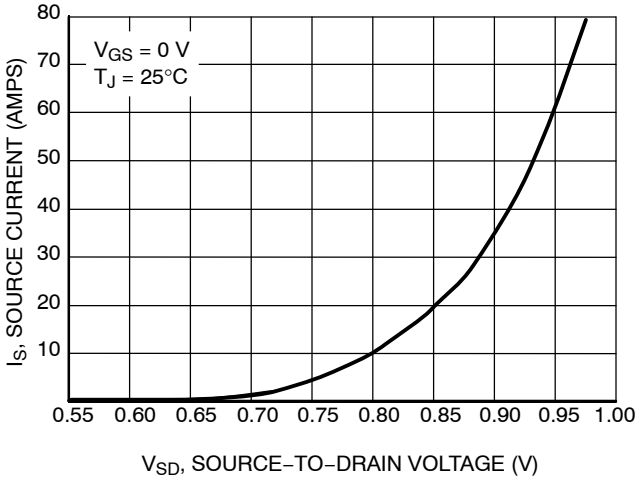


Figure 10. Diode Forward Voltage versus Current

NTD80N02

TYPICAL CHARACTERISTICS

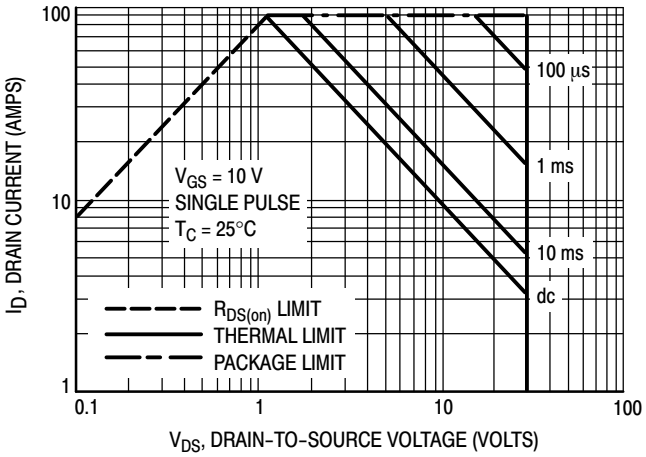


Figure 11. Maximum Rated Forward Biased Safe Operating Area

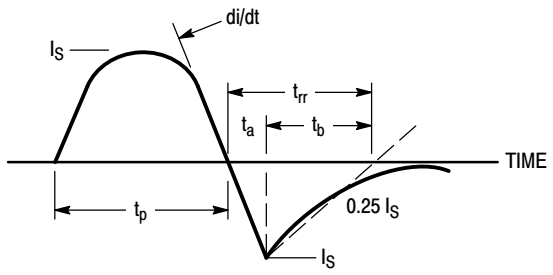


Figure 12. Diode Reverse Recovery Waveform

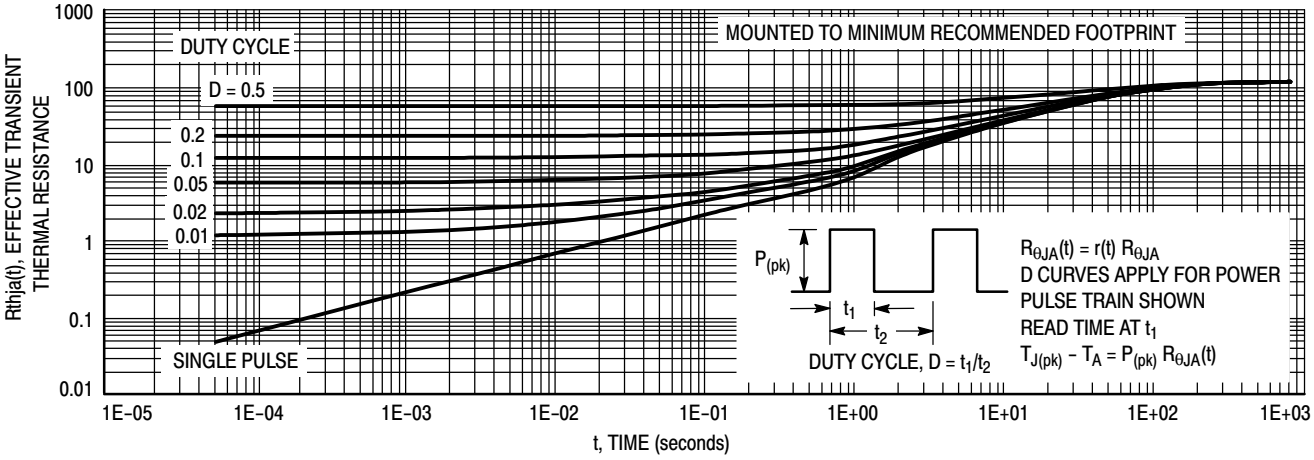


Figure 13. Thermal Response − Various Duty Cycles

ORDERING INFORMATION

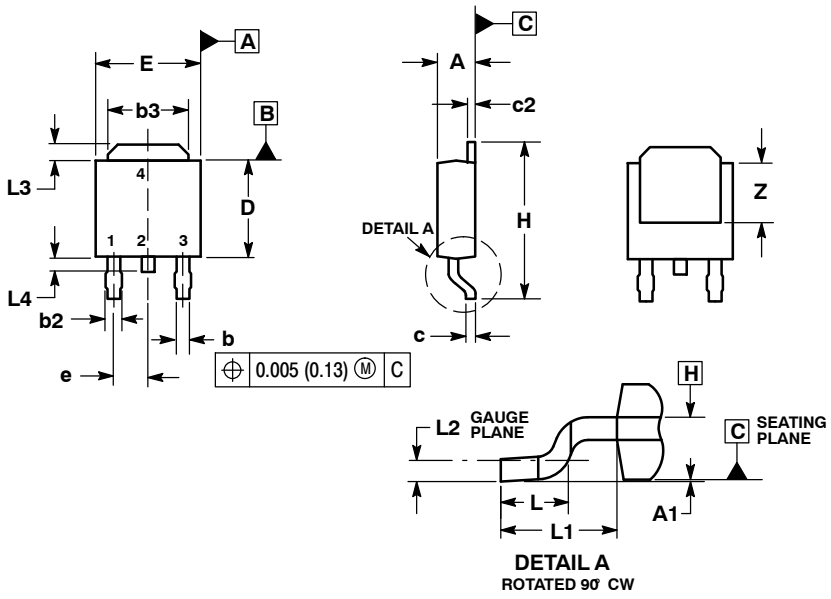
Order Number	Package	Shipping†
NTD80N02T4G	DPAK−3 (Pb−Free)	2500 / Tape & Reel
NTD80N02−1G	DPAK−3 Straight Lead (Pb−Free)	75 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD80N02

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)
CASE 369AA−01
ISSUE B

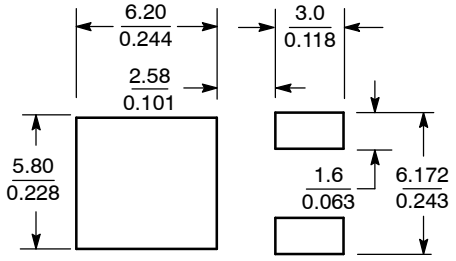


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



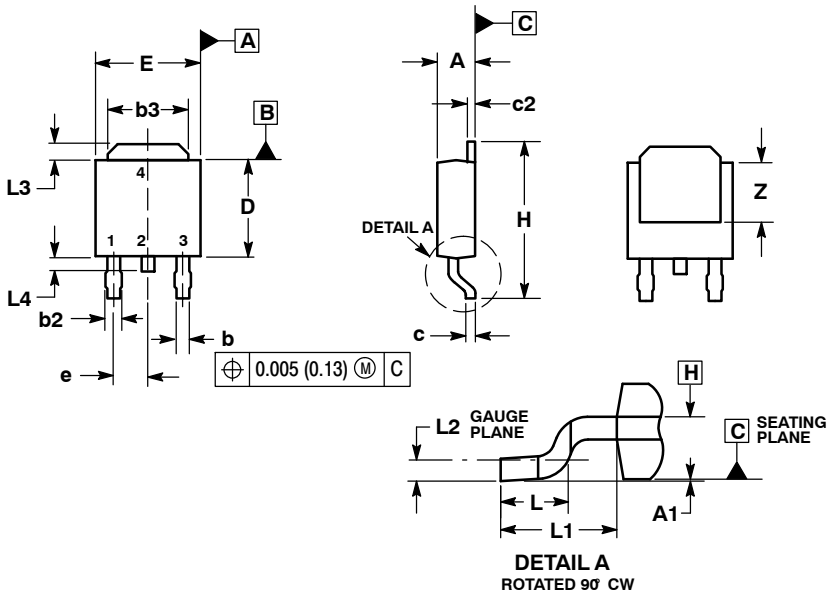
SCALE 3:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD80N02

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)
CASE 369C−01
ISSUE D



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

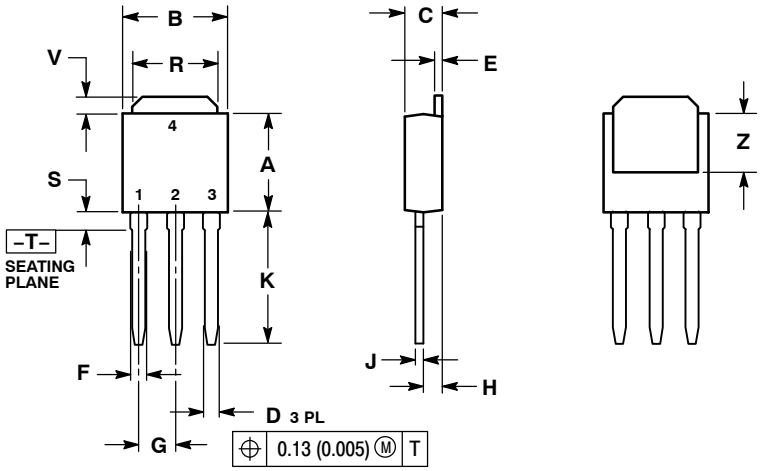
	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NTD80N02

PACKAGE DIMENSIONS

DPAK
CASE 369D−01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

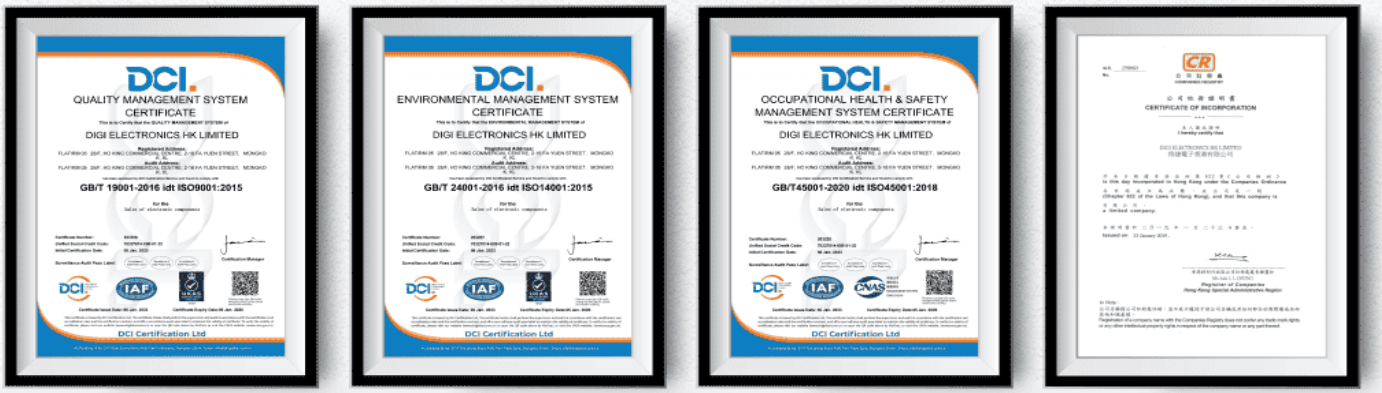
Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

NTD80N02/D

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.